



TPS65560

SLVS608-JANUARY 2006

INTEGRATED PHOTO FLASH CHARGER AND IGBT DRIVER

FEATURES

- Highly Integrated Solution to Reduce Components
- Integrated Voltage Reference
- Integrated 50-V Power Switch,
- Integrated IGBT Driver
- High Efficiency
- Programmable Peak Current, 0.9 A ~ 1.8 A
- Input Battery Voltage of 1.6 V to 12 V
- Optimized Control Loop for Fast Charge Time
- Output Voltage Feedback From Primary Side
- 16-Pin QFN Package
- Protection
 - MAX On Time
 - MAX Off Time
 - Overcurrent Shutdown to Monitor V_{DS} at the SW pin (OV_{DS})
 - Thermal Disable

APPLICATIONS

- Digital Still Cameras
- Optical Film Cameras
- Mobile Phones With Camera
- PDAs With Camera

DESCRIPTION

This device offers a complete solution for charging a photo flash capacitor from battery input, and subsequently discharging the capacitor to a xenon flash tube. The device has an integrated voltage reference, power switch, IGBT driver, and control logic blocks for charging applications and driving IGBT applications. Compared with discrete solutions, this device reduces the component count, shrinks the solution size, and eases designs for xenon tube applications. Additional advantages are a fast charging time and high efficiency from an optimized PWM control algorithm.

Other provisions of the device includes sensing the output voltage from the primary side, programmable peak current, thermal shutdown, an output pin for charge completion, and input pins for charge enable and flash enable.

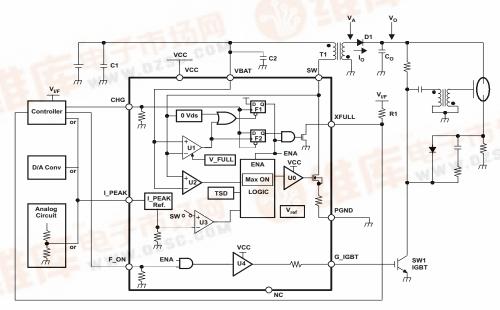


Figure 1. Typical Application Circuit

Phease be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

PowerPAD is a trademark of Texas Instruments.





These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ORDERING INFORMATION

T _A	T _A PACKAGE MARKING		PART NUMBER	
-35°C to 85°C	BPR	16-pin QFN	TPS65560RGT	

For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI Web site at www.ti.com.

ABSOLUTE MAXIMUM RATINGS

over operating free-air temperature range (unless otherwise noted) (1)

			UNIT
	Complexed	VCC	-0.6 V to 6 V
V_{SS}	Supply voltage	VBAT	-0.6 V to 13 V
V _(SW)	Switch terminal voltage	ge	-0.6 V to 50 V
I _(SW)	Switch current between	en SW and PGND, ISW	3 A
VI	Input voltage of CHG	, I_PEAK, F_ON	-0.3 V to V _{CC}
T _{stg}	Storage temperature		-40°C to 150°C
T _J	Maximum junction ter	mperature	125°C
	ESD rating	HBM (Human Body Model) JEDEC JES22-A114	1 kV

⁽¹⁾ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

RECOMMENDED OPERATING CONDITIONS

		MIN	NOM MAX	UNIT
V	Supply voltage, VCC	2.7	4	V
V _{SS}	Supply voltage, VBAT	1.6	12	V
V _(SW)	Switch terminal voltage,	-0.3	45	V
I _(SW)	Switch current between SW and PGND		2	Α
	Operating free-air temperature range	-35	85	°C
V_{IH}	High-level digital input voltage at CHG and F_ON	2		V
V _{IL}	Low-level digital input voltage at CHG and F_ON		0.5	V

DISSIPATION RATINGS

PACKAGE	R _{θJA} ⁽¹⁾	POWER RATING T _A < 25°C	POWER RATING T _A = 70°C	POWER RATING T _A = 85°C
QFN	47.4 °C/W	2.11 W	1.16 W	844 mW

(1) The thermal resistance, $R_{\theta JA}$, is based on a soldered PowerPADTM on a 2S2P JEDEC board using thermal vias.



ELECTRICAL CHARACTERISTICS

 $T_A = 25$ °C, VBAT = 4.2 V, VCC = 3 V, $V_{(SW)} = 4.2$ V (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT			
R _(ONL)	ON resistance of XFULL	I _(XFULL) = -1 mA		1.5	3	kΩ			
V _(PKH) ⁽¹⁾	Upper threshold voltage of I_PEAK	V _{CC} = 3 V	2.4			V			
V _(PKL) ⁽¹⁾	Lower threshold voltage of I_PEAK	V _{CC} = 3 V			0.6	V			
I _{CC1}	Supply current from VBAT	CHG = H, $V_{(SW)} = 0 \text{ V}$ (free run by t_{MAX})		17	50	μΑ			
I _{CC2}	Supply current from VCC	CHG = H, $V_{(SW)} = 0 \text{ V}$ (free run by t_{MAX})		1.3	3	mA			
I _{CC3}	Supply current from VCC and VBAT	CHG = L			1	μΑ			
I _{lkg1}	Leakage current of SW terminal				2	μΑ			
I _{lkg2}	Leakage current of XFULL terminal	V _(XFULL) = 5 V			1	μΑ			
	Sink current at I PEAK	V _(I_PEAK) = 3 V, CHG: High			2	^			
I _(sink)	Sink current at I_FEAR	V _(I_PEAK) = 3 V, CHG: Low			0.1	μΑ			
R _(ONSW)	SW ON resistance between SW and PGND	I _(SW) = 1 A, V _{CC} = 3 V		0.4	0.9	Ω			
R _(IGBT1)	G_IGBT pullup resistance	$V_{(G_IGBT)} = 0 \text{ V}, V_{CC} = 3 \text{ V}$	8	12	19.4	Ω			
R _(IGBT2)	G_IGBT pulldown resistance	$V_{(G_IGBT)} = 3 \text{ V}, V_{CC} = 3 \text{ V}$	36	53	70	Ω			
I _(PEAK1)	Upper peak of I _(SW)	V _(I_IPEAK) = 3 V	1.58	1.68	1.78	Α			
I _(PEAK2)	Lower peak of I _(SW)	$V_{(I_IPEAK)} = 0 V$	0.7	0.8	0.9	Α			
\/	Charge completion detect voltage	VBAT = 1.6V, V _{CC} = 3 V	28	28.7	29.4	V			
$V_{(FULL)}$	at V _(SW)	V _{CC} = 3 V	28.6	29	29.4	V			
V _(ZERO)	Zero current detection at V _(SW)		1	20	60	mV			
T _(SD) ⁽¹⁾	Thermal shutdown temperature		150	160	170	°C			
·	Over V _{DS} detection at V _(SW)		0.95	1.2	1.45	V			
t _{MIN}	MAX OFF time		25	50	80	μs			
t _{MAX}	MAX ON time		50	100	160	μs			
R _(INPD)	Pulldown resistance of CHG, F_ON	VCHG = V _(F_ON) = 4.2 V		100		kΩ			

⁽¹⁾ Specified by design.

SWITCHING CHARACTERISTICS

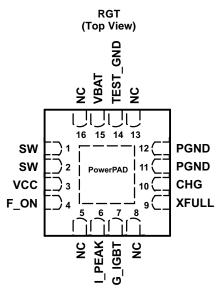
 $T_A = 25$ °C, VBAT = 4.2 V, VCC = 3 V, $V_{(SW)} = 4.2$ V (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP MAX	UNIT
		F_ON↑↓ - G_IGBT↑↓		50	ns
		SW ON after V _(SW) dips from V _(ZERO)		45	ns
t _{PD} ⁽¹⁾	Propagation delay	SW OFF after I _(SW) exceeds I _(PEAK)		270	ns
'PD'''	Propagation delay	XFULL↓ after V _(SW) exceeds V _(FULL)		400	ns
		SW ON after CHG↑		12	μs
		SW OFF after CHG↓		20	ns

(1) Specified by design.



PIN ASSIGNMENT



NC - No internal connection

TERMINAL FUNCTIONS

PIN NUMBER	SIGNAL	1/0	DESCRIPTION
1, 2	SW	0	Primary side switch. Connect SW to the switched side of the transformer
3	vcc	I	Power supply input. Connect VCC to an input supply from 2.7 V to 4 V. Bypass VCC to GND with a $1-\mu F$ ceramic capacitor as close as possible to the IC.
4	F_ON	I	G_IGBT control input. Drives F_ON with the flash discharge signal. A logic high on F_ON drives G_IGBT high when CHG is Low. See the <i>IGBT Driver Conrtol</i> section for details.
5, 8, 13, 16	NC		No internal connection
6	I_PEAK	I	Primary side peak current control input. The voltage at I_PEAK sets the peak current into SW. See the <i>Programming Peak Current</i> section for details on selecting V _(I_PEAK) .
7	G_IGBT	0	IGBT gate driver output. G_IGBT swings from PGND to VCC to drive external IGBT devices.
9	XFULL	0	Charge completion indicator output. XFULL is an open-drain output that pulls low once the output is fully charged. XFULL is high impedance during charging and all fault conditions. XFULL is reseted when CHG turns Low from High. See the <i>Indicating Charging Status</i> section for details.
10	CHG	I	Charge control input. Drive CHG high to initiate charging of the output. Drive CHG low to terminate charging.
11, 12	PGND		Power ground. Connect to the ground plane.
14	TEST_GND		Used by TI, should be connected to PGND and ground plane.
15	VBAT	I	Battery voltage monitor input. Connect VBAT to an input supply from 1.6 V to 12 V. Bypass VBAT to GND with a 10- μ F ceramic capacitor (C1 in Figure 1, as close as possible to the battery) and a 1- μ F ceramic capacitor (C2 in Figure 1, as close as possible to the IC).



FUNCTIONAL BLOCK DIAGRAM

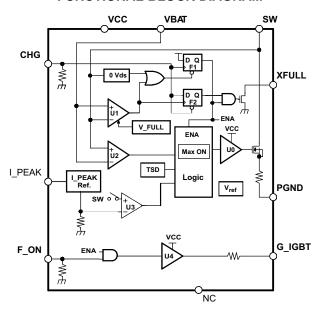


Figure 2. Functional Block Diagram

I/O Equivalent Circuits

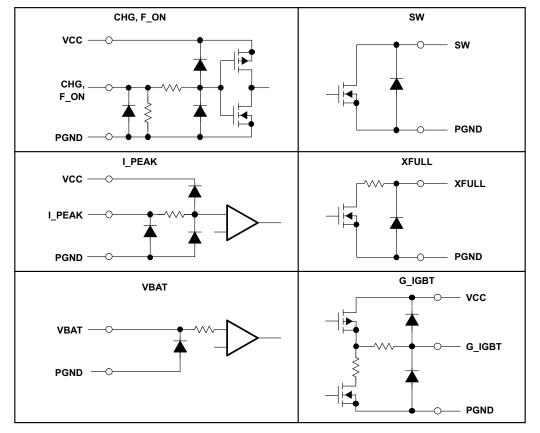


Figure 3. I/O Equivalent Circuits



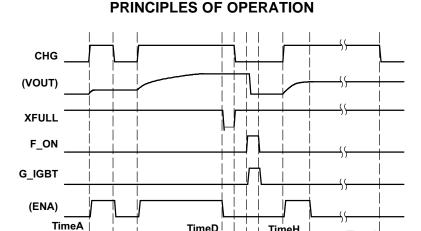


Figure 4. Whole Operation Sequence Chart

TimeD |

TimeE |

TimeF TimeG TimeH

Timel

TimeJ

Start/Stop Charging

TPS65560 has one internal enable latch, F1, that holds the charge enable (ON/OFF status) of the device. See Figure 2.

The only way to start charging is to input CHG↑ (see time A/C/H in Figure 4). Each time CHG↑ is applied, the TPS65560 starts charging.

There are three trigger events to stop charging:

1. Forced stop by inputting CHG = L from the controller (see timeB in Figure 4).

TimeB

TimeC

- 2. Automatic stop by detecting a full charge. VOUT reaches the target value (see TimeD in Figure 4).
- 3. Protected *stop* by detecting an over current function (OV_{DS}) trigger at SW pin (see Timel in Figure 4).

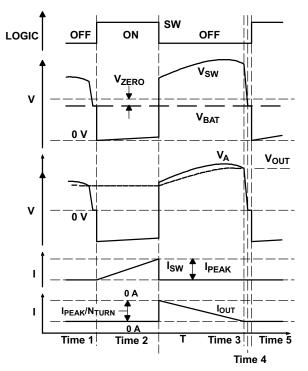
Indicating Charging Status

When the charging operation is complete, the TPS65560 drives the charge completion indicator pin, XFULL, to GND. A controller can detect the status of the device as a logic signal when connected through a pullup resister, R1 (see Figure 1).

The XFULL output enables the controller to detect the OV_{DS} protection status. If OV_{DS} protection occurs, XFULL never goes L during CHG = H. Therefore, the controller detects OV_{DS} protection by measuring the time from CHG high to XFULL low. If the time to XFULL low is longer than the maximum designed charge time, then an OV_{DS} protection occurred.

The device starts charging at timeH, and OV_{DS} protection occurs at TimeI (see Figure 4). At TimeI, XFULL stays H. At TimeJ, the controller detects OV_{DS} protection through the expiration of a timer ends and then sets CHG to low to terminate the operation.





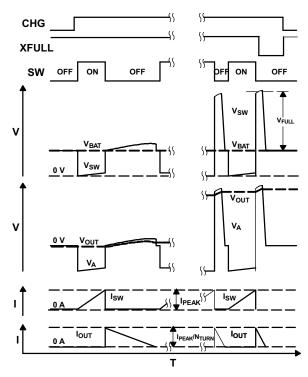


Figure 5. Timing Diagram at One Switching Cycle

Figure 6. Timing Diagram at Beginning/Ending

Control Charging

The TPS65560 provides three comparators to control charging. Figure 2 shows the block diagram of TPS65560 and Figure 5 shows a timing diagram of one switch cycle. Note that emphasis is placed on Time1 and Time3 of the waveform in Figure 5.

While SW is ON (Time1 to Time2 in Figure 5), U3 monitors current flow through the integrated power switch from SW pin to GND. When $I_{(SW)}$ exceeds $I_{(PEAK)}$, SW turns OFF (Time2 in Figure 5).

When SW turns OFF (Time2 in Figure 5), the magnetic energy in the transformer starts discharging. Meanwhile, U2 monitors the kickback voltage at the SW terminal. As the energy is discharging, the kickback voltage is increasing according to the increase of V_O (Time2 to Time3 in Figure 5). When almost all energy is discharged, the system cannot continue rectification via the diode, and the charging current of I_O goes to zero (Time3 in Figure 5). After rectification stops, the small amount of energy left in the transformer is released via parasitic paths, and the kickback voltage reaches zero (Time3 to Time4 in Figure 5). During this period, U2 makes SW turn ON when $(V_{(SW)} - V_{BAT})$ dips from $V_{(ZERO)}$ (Time5 in Figure 5). In the actual circuit, the period between Time4 and Time5 in Figure 5 is small or does not appear dependent on the delay time of the U2 detection to SW ON.

U1 also monitors the kickback voltage. When $(V_{(SW)} - V_{BAT})$ exceeds $V_{(FULL)}$, the TPS65560 stops charging (see Figure 6).

In Figure 5 and Figure 6, ON time is always the same period in every switch cycle. The ON time is calculated by Equation 1. L and $I_{(PEAK)}$ are selected to ensure that t_{ON} does not exceed the MAX ON time (t_{MAX}).

$$t_{ON} = L \frac{I_{PEAK}}{V_{BAT}}$$
 (1)



The *OFF* time is dependant on output voltage. As the output voltage gets higher, the *OFF* time gets shorter (see Equation 2).

$$t_{OFF} = N_{TURN} \times L \frac{I_{PEAK}}{V_{OUT}}$$
 (2)

Programming Peak Current

The TPS65560 provides a method to program the peak primary current with a voltage applied to the I_PEAK pin. Figure 7 shows how to program $I_{(PEAK)}$.

The I_PEAK input is treated as a logic input below $V_{(PKL)}$ (0.6 V) and above $V_{(PKH)}$ (2.4 V). Between $V_{(PKL)}$ and $V_{(PKH)}$, I_PEAK input is treated as an analog input. Using this characteristic, $I_{(PEAK)}$ can be set by a logic signal or by an analog input.

Typical usages of this function are:

- 1. Setting the peak charging currents based on the battery voltage. Larger I_(PEAK) for a fully charged battery and lower I_(PEAK) for a discharged battery.
- 2. Reducing $I_{(PEAK)}$ when powering a zooming lens motor. This avoids inadvertent shutdowns due to large current from the battery.

In Figure 1, three optional connections to I_PEAK are shown.

- 1. Use the controller to treat I_PEAK as the logic input pin. This option is the easiest.
- 2. Use a D/A converter to force I_(PEAK) to follow analog information, such as battery voltage.
- 3. Use an analog circuit to achieve the same results as the D/A converter.

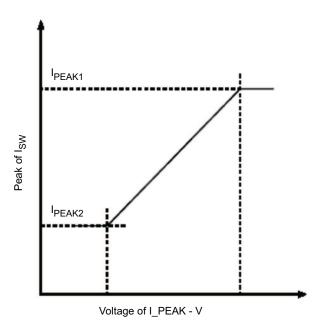


Figure 7. I_PEAK vs I_(SW)



IGBT Driver Control

The IGBT driver is provided by the TPS65560. The driver voltage depends on VCC. TPS65560 has a mask filter as shown in Figure 8. The mask does not have hysteresis; therefore, there is no wait time from CHG forcing Low after FULL CHARGE to F_ON turning High.

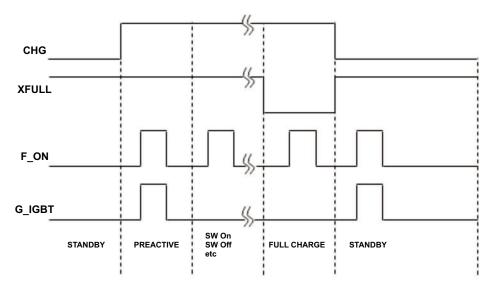


Figure 8. IGBT Timing Diagram

Protections

TPS65560 provides four protection mechanisms: max on time, max off time, thermal disable, and overcurrent shutdown.

MAX On Time

To prevent a condition such as pulling current from a poor power source (i.e., an almost empty battery), and never reaching peak current, the TPS65560 provides a maximum ON time function. If the ON time exceeds t_{MAX} , the TPS5560 is forced OFF regardless of $I_{(PEAK)}$ detection.

MAX Off Time

To prevent a condition such as never increasing the voltage at the SW pin when the internal FET is OFF, the TPS65560 provides a maximum OFF time function. If the *OFF* time exceeds t_{MIN} , the TPS65560 is forced ON regardless of $V_{(ZERO)}$ detection.

Thermal Disable

Once the TPS65560 die temperature reaches 160°C, all functions stop. Once the die cools below 160°C, the TPS65560 restarts charging if CHG remains high during the entire overtemperature condition.

Overcurrent Shutdown to Monitor V_{DS} at the SW Pin (OV_{DS})

The TPS65560 provides an overvoltage monitor function of the SW pin. The TPS65560 is latched off if the voltage on the SW pin is above OV_{DS} during the switch ON time (see Figure 4 and its descriptions).

This function protects against short-circuits on the primary side of the transformer. A short-circuit of the primary side shorts the battery voltage to GND. SW pin can damage the device if not protected.



PACKAGE OPTION ADDENDUM

14-Mar-2006

PACKAGING INFORMATION

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	e Eco Plan ⁽²⁾	Lead/Ball Finish	MSL Peak Temp ⁽³⁾
TPS65560RGTR	ACTIVE	QFN	RGT	16	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
TPS65560RGTRG4	ACTIVE	QFN	RGT	16	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
TPS65560RGTT	ACTIVE	QFN	RGT	16	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
TPS65560RGTTG4	ACTIVE	QFN	RGT	16	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

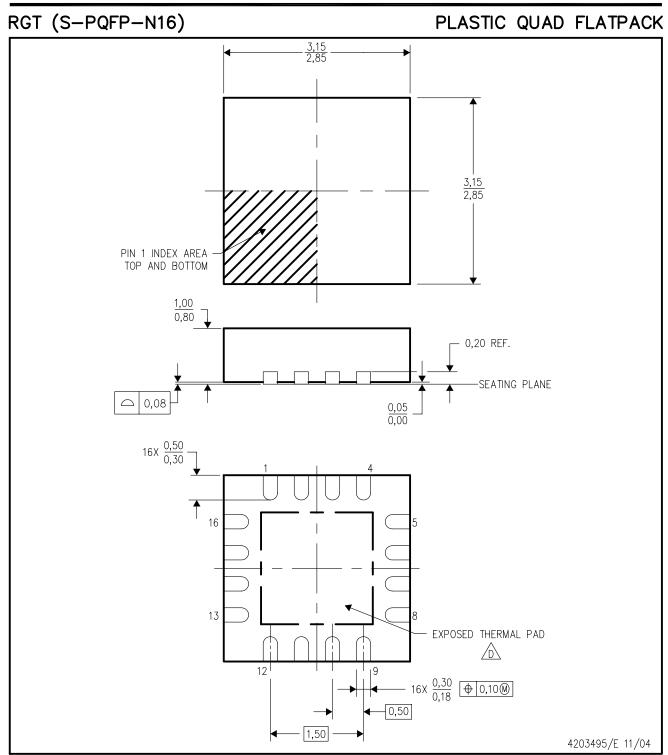
Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.



NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M—1994.

- B. This drawing is subject to change without notice.
- C. Quad Flatpack, No-leads (QFN) package configuration.
- The package thermal pad must be soldered to the board for thermal and mechanical performance. See the Product Data Sheet for details regarding the exposed thermal pad dimensions.
- E. Falls within JEDEC MO-220.





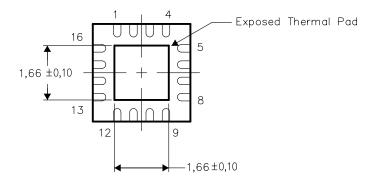
THERMAL PAD MECHANICAL DATA RGT (S-PQFP-N16)

THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to a ground or power plane (whichever is applicable), or alternatively, a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No—Lead (QFN) package and its advantages, refer to Application Report, Quad Flatpack No—Lead Logic Packages, Texas Instruments Literature No. SCBA017. This document is available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



Bottom View

NOTE: All linear dimensions are in millimeters

Exposed Thermal Pad Dimensions

IMPORTANT NOTICE

Texas Instruments Incorporated and its subsidiaries (TI) reserve the right to make corrections, modifications, enhancements, improvements, and other changes to its products and services at any time and to discontinue any product or service without notice. Customers should obtain the latest relevant information before placing orders and should verify that such information is current and complete. All products are sold subject to TI's terms and conditions of sale supplied at the time of order acknowledgment.

TI warrants performance of its hardware products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are used to the extent TI deems necessary to support this warranty. Except where mandated by government requirements, testing of all parameters of each product is not necessarily performed.

TI assumes no liability for applications assistance or customer product design. Customers are responsible for their products and applications using TI components. To minimize the risks associated with customer products and applications, customers should provide adequate design and operating safeguards.

TI does not warrant or represent that any license, either express or implied, is granted under any TI patent right, copyright, mask work right, or other TI intellectual property right relating to any combination, machine, or process in which TI products or services are used. Information published by TI regarding third-party products or services does not constitute a license from TI to use such products or services or a warranty or endorsement thereof. Use of such information may require a license from a third party under the patents or other intellectual property of the third party, or a license from TI under the patents or other intellectual property of TI.

Reproduction of information in TI data books or data sheets is permissible only if reproduction is without alteration and is accompanied by all associated warranties, conditions, limitations, and notices. Reproduction of this information with alteration is an unfair and deceptive business practice. TI is not responsible or liable for such altered documentation.

Resale of TI products or services with statements different from or beyond the parameters stated by TI for that product or service voids all express and any implied warranties for the associated TI product or service and is an unfair and deceptive business practice. TI is not responsible or liable for any such statements.

Following are URLs where you can obtain information on other Texas Instruments products and application solutions:

Products		Applications	
Amplifiers	amplifier.ti.com	Audio	www.ti.com/audio
Data Converters	dataconverter.ti.com	Automotive	www.ti.com/automotive
DSP	dsp.ti.com	Broadband	www.ti.com/broadband
Interface	interface.ti.com	Digital Control	www.ti.com/digitalcontrol
Logic	logic.ti.com	Military	www.ti.com/military
Power Mgmt	power.ti.com	Optical Networking	www.ti.com/opticalnetwork
Microcontrollers	microcontroller.ti.com	Security	www.ti.com/security
		Telephony	www.ti.com/telephony
		Video & Imaging	www.ti.com/video
		Wireless	www.ti.com/wireless

Mailing Address: Texas Instruments

Post Office Box 655303 Dallas, Texas 75265